

OBSOLETE – PART DISCONTINUED

## Description

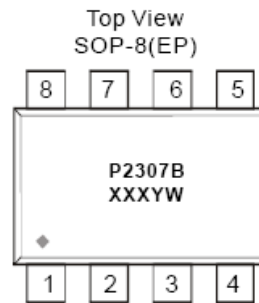
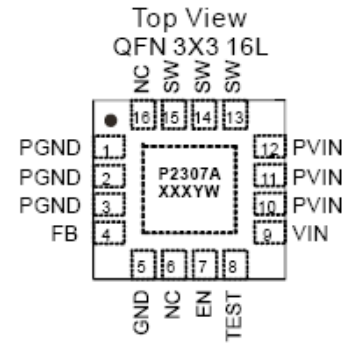
The PAM2307 is a 3A step-down DC-DC converter. At heavy load, the constant-frequency PWM control performs excellent stability and transient response. No external compensation components are required.

The PAM2307 supports a range of input voltages from 2.7V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, and other standard power sources. The output voltage is adjustable from 0.6V to the input voltage. The PAM2307 employs internal power switch and synchronous rectifier to minimize external part count and realize high efficiency. During shutdown, the input is disconnected from the output and the shutdown current is less than 1µA. Other key features include over-temperature and short circuit protection, and under-voltage lockout to prevent deep battery discharge.

The PAM2307 delivers 3A maximum output current while consuming only 42µA of no-load quiescent current. Ultra-low  $R_{DS(ON)}$  integrated MOSFETs and 100% duty cycle operation make the PAM2307 an ideal choice for high output voltage, high current applications which require a low dropout threshold.

The PAM2307 is available in QFN3x3 16-Pin and SOP-8(EP) package.

## Pin Assignments



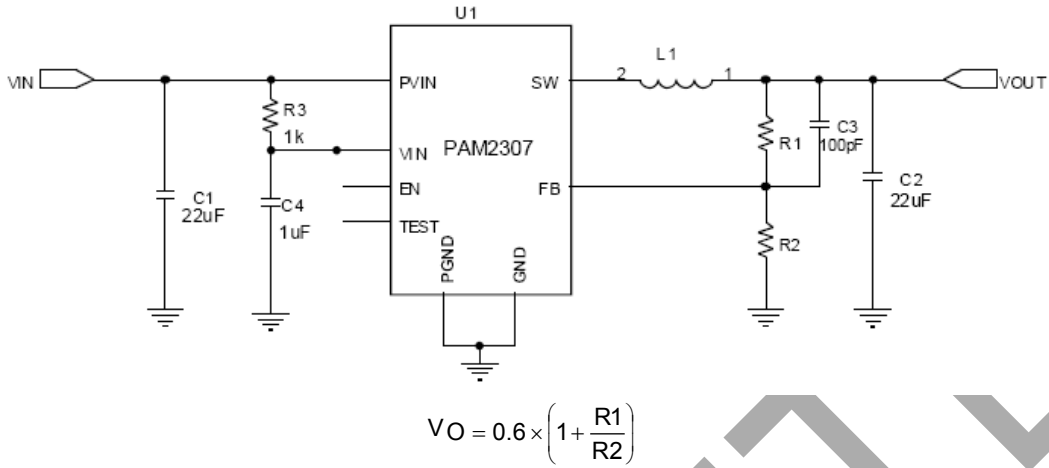
## Features

- Output Current: Up to 3A
- Output Voltage: 0.6V to  $V_{IN}$
- Input Voltage: 2.7 to 5.5V
- Efficiency up to 95%
- 42µA (Typ) No Load Quiescent Current
- Shutdown Current: <1µA
- 100% Duty Cycle Operation
- 1.5MHz Switching Frequency
- Internal Soft Start
- No External Compensation Required
- Current Limit Protection
- Thermal Shutdown
- QFN3x3 16-Pin and SOP-8(EP) Package

## Applications

- 5V or 3.3V Point of Load Conversion
- Telecom/Networking Equipment
- Set Top Boxes
- Storage Equipment
- Video Cards
- DDR Power Supply

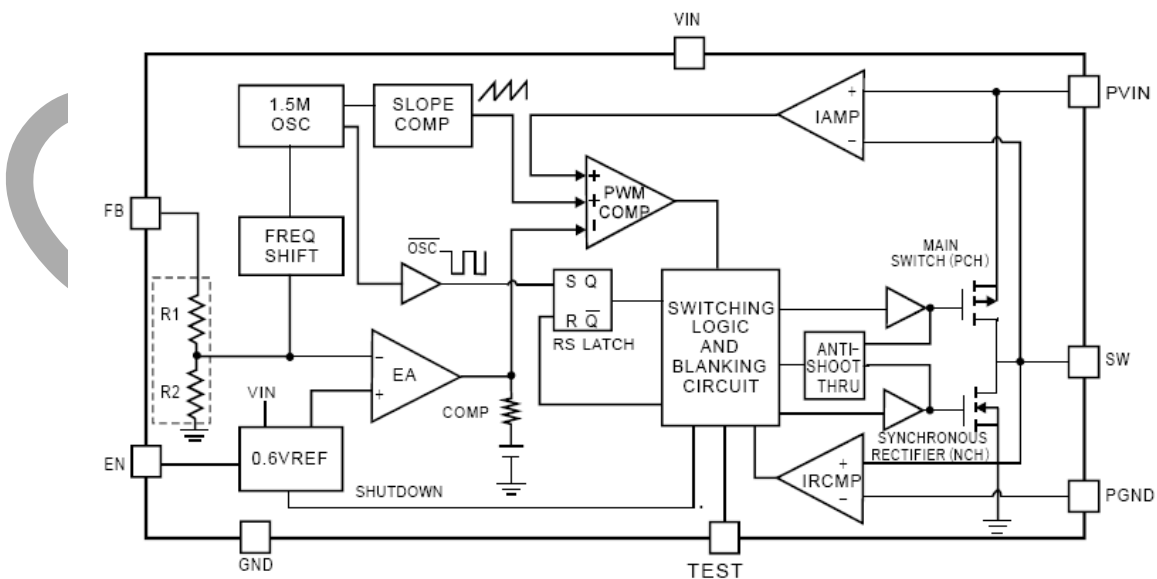
**Typical Applications Circuit**



**Pin Descriptions**

Pin Name	Package Name		Function
	QFN3x3-16L	SOP-8(EP)	
PGND	1, 2, 3	2	Main power ground pin.
FB	4	3	Feedback voltage to internal error amplifier, the threshold voltage is 0.6V.
GND	5	4	Signal ground for small signal components.
NC	6, 16	—	No connection.
EN	7	5	Enable control input. Force this pin voltage above 1.5V, enables the chip, and below 0.3V shuts down the device.
TEST	8	6	Test Mode (no connect or to Ground).
VIN	9	7	Bias supply. Chip main power supply pin.
PVIN	10, 11, 12	8	Input supply for power stage. Must be closely decoupled to PGND.
SW	13, 14, 15	1	The drains of the internal main and synchronous power MOSFET.

**Functional Block Diagram**



### Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability. All voltages are with respect to ground.

Parameter	Rating	Unit
Input Voltage $PV_{IN}, V_{IN}$	6	V
SW Pin Voltage	-0.3 to $(PV_{IN} + 0.3)$	V
FB Pin Voltage	-0.3 to $(V_{IN} + 0.3)$	V
EN Pin Voltage	-0.3 to +6.0	V
Maximum Junction Temperature	150	$^\circ\text{C}$
Storage Temperature Range	-65 to +150	$^\circ\text{C}$
Soldering Temperature	300, 5sec	$^\circ\text{C}$

### Recommended Operating Conditions (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Parameter	Rating	Unit
Supply Voltage	2.5 to 5.5	V
Junction Temperature Range	-40 to +125	$^\circ\text{C}$
Ambient Temperature Range	-40 to +85	

### Thermal Information

Parameter	Symbol	Package	Max	Unit
Thermal Resistance (Junction to Ambient)	$\theta_{JA}$	QFN3x3-16	35	$^\circ\text{C/W}$
		SOP-8(EP)	90	
Thermal Resistance (Junction to Case)	$\theta_{JC}$	QFN3x3-16	14	
		SOP-8(EP)	11	

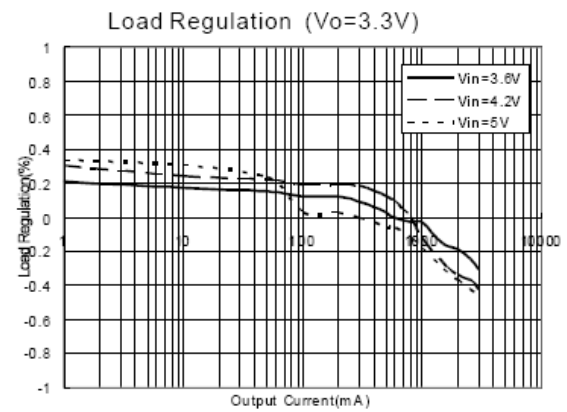
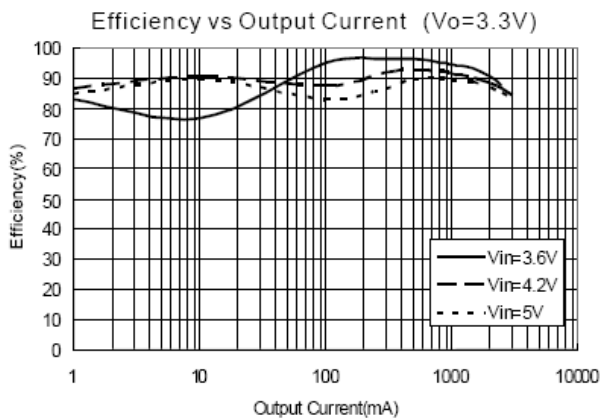
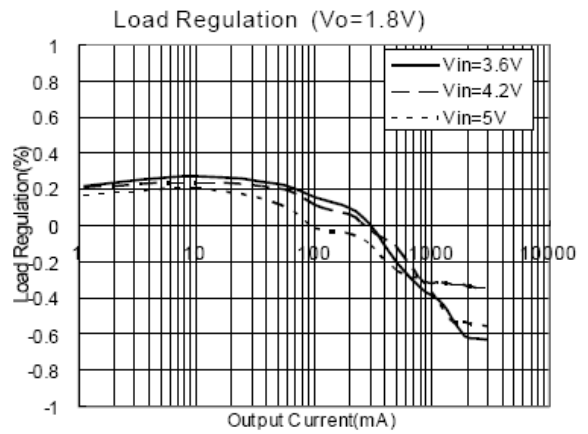
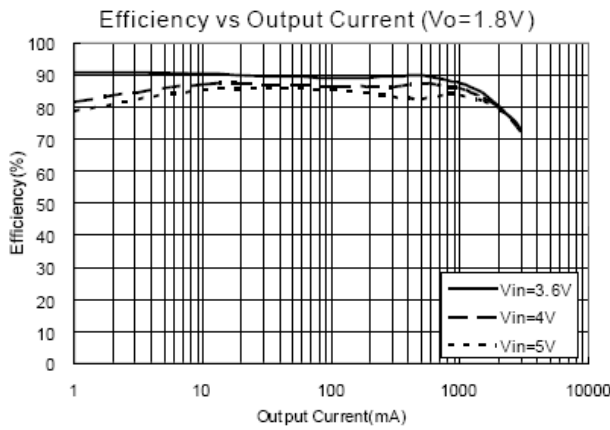
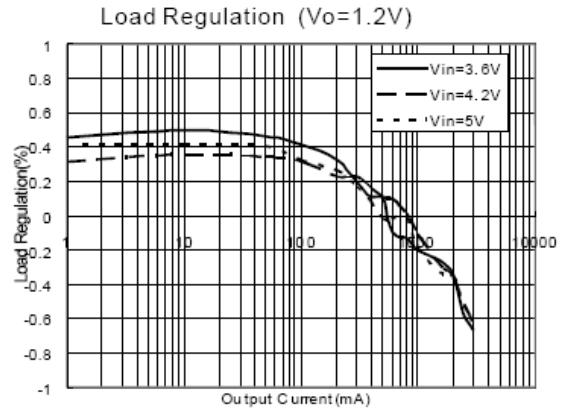
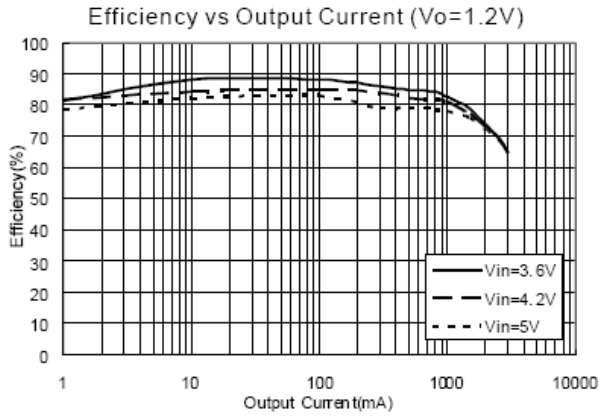
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, V<sub>IN</sub> = 3.6V, V<sub>O</sub> = 1.8V, C<sub>IN</sub> = 22μF, C<sub>O</sub> = 22μF, L = 2.2μH, unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Input Voltage Range	V <sub>IN</sub>		2.5		5.5	V
Output Voltage Range	V <sub>O</sub>		0.6		V <sub>IN</sub>	V
UVLO Threshold	V <sub>UVLO</sub>	V <sub>IN</sub> Rising		2.4	2.5	V
		Hysteresis		240		mV
		V <sub>IN</sub> Falling	1.8			V
Regulated Output Voltage Accuracy	V <sub>O</sub>	I <sub>O</sub> = 0 to 3A, V <sub>IN</sub> = 2.5 to 5.5V	-2		+2	%
Regulated Feedback Voltage	V <sub>FB</sub>		0.588	0.600	0.612	V
FB Leakage Current	I <sub>FB</sub>	V <sub>O</sub> = 1V			0.2	μA
Output Voltage Line Regulation	LNR	V <sub>IN</sub> = 2.5V to 5V		0.2		%/V
Output Voltage Load Regulation	LDR	I <sub>O</sub> = 0A to 3A		0.5		%/A
Quiescent Current	I <sub>Q</sub>	No Load		42	90	μA
Shutdown Current	I <sub>SD</sub>	V <sub>EN</sub> = 0V			1	μA
Current Limit	I <sub>LIM</sub>			3.5		A
Oscillator Frequency	f <sub>OSC</sub>		1.2	1.5	1.8	MHz
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	High Side		0.140		Ω
		Low Side		0.09		Ω
High Efficiency	η				95	%
Start-Up Time	t <sub>S</sub>	From enable to output regulation			3	ms
EN Threshold High	V <sub>EH</sub>		1.5			V
EN Threshold Low	V <sub>EL</sub>				0.3	V
EN Leakage Current	I <sub>EN</sub>	V <sub>IN</sub> = V <sub>EN</sub> = 0V	-1.0		+1.0	μA
Over Temperature Protection	OTP			150		°C
OTP Hysteresis	OTH			30		°C

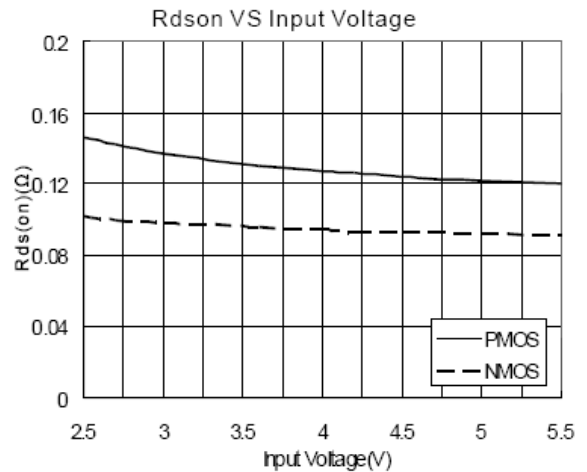
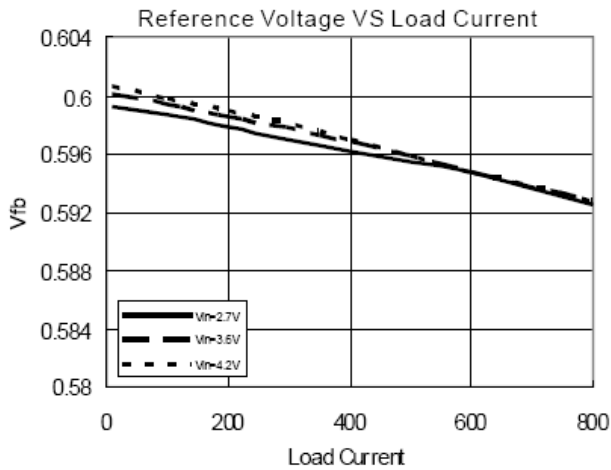
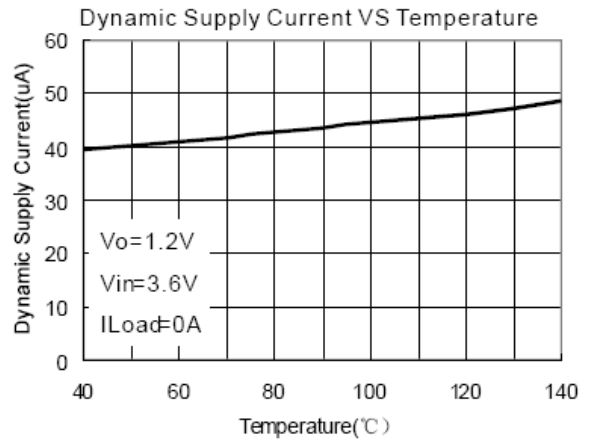
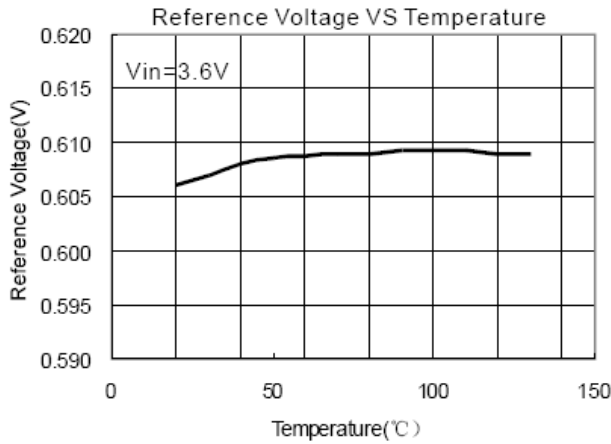
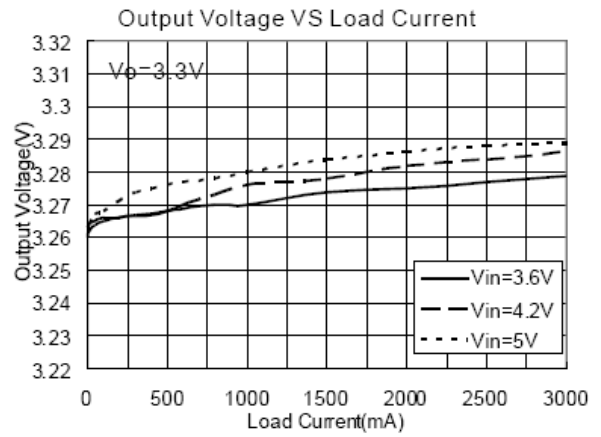
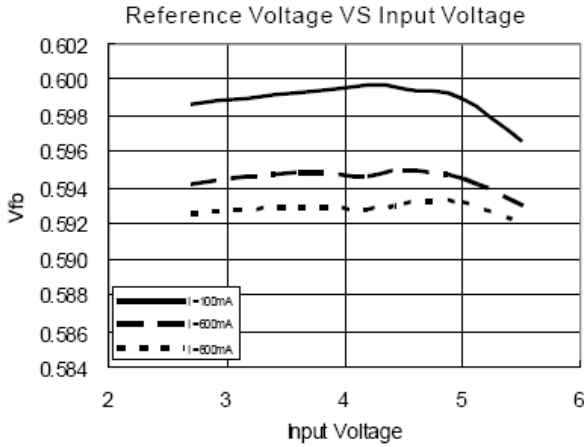
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**Typical Performance Characteristics** (@ $T_A = +25^\circ\text{C}$ ,  $C_{IN} = 22\mu\text{F}$ ,  $C_O = 22\mu\text{F}$ , unless otherwise specified.)

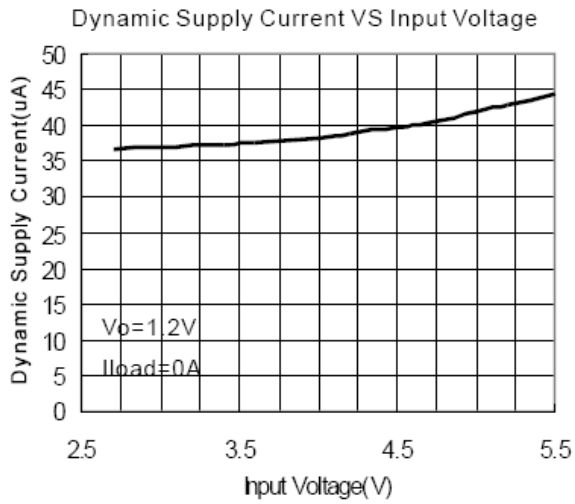
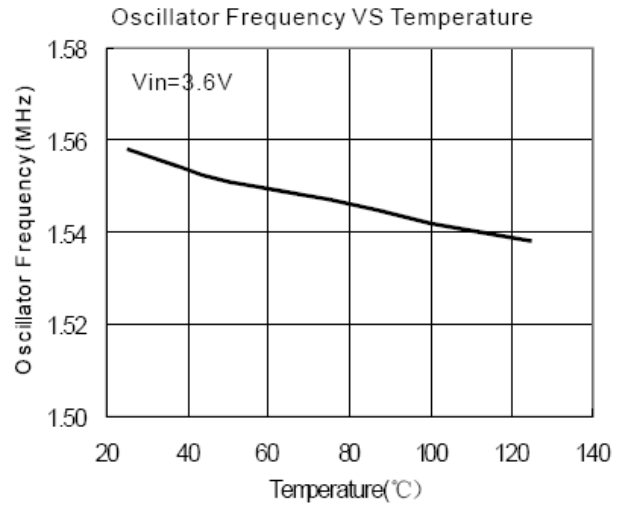
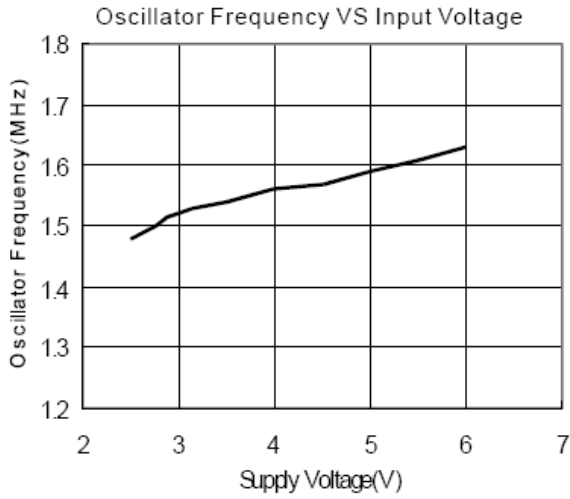
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**Typical Performance Characteristics** (cont.) (@ $T_A = +25^\circ\text{C}$ ,  $C_{IN} = 22 \times 2\mu\text{F}$ ,  $C_O = 22\mu\text{F}$ , unless otherwise specified.)

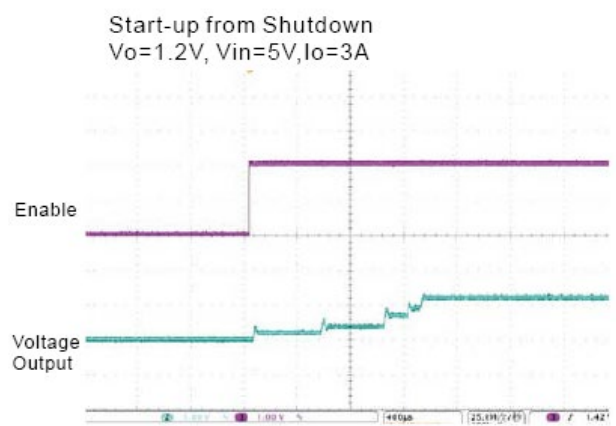
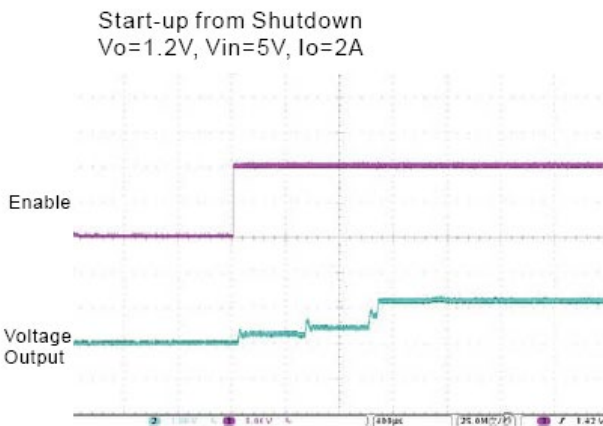
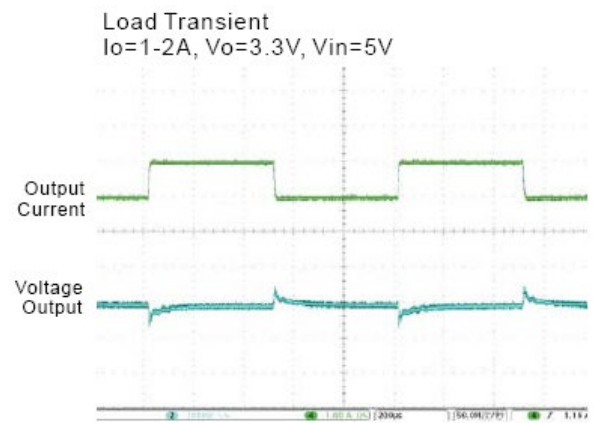
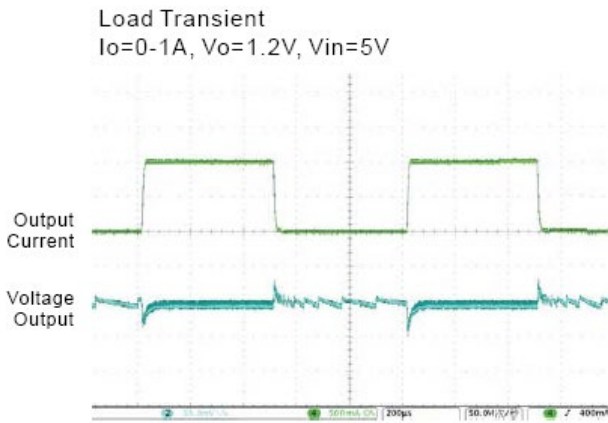
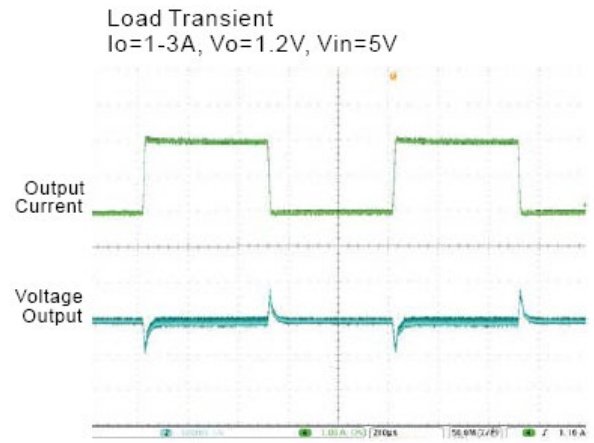
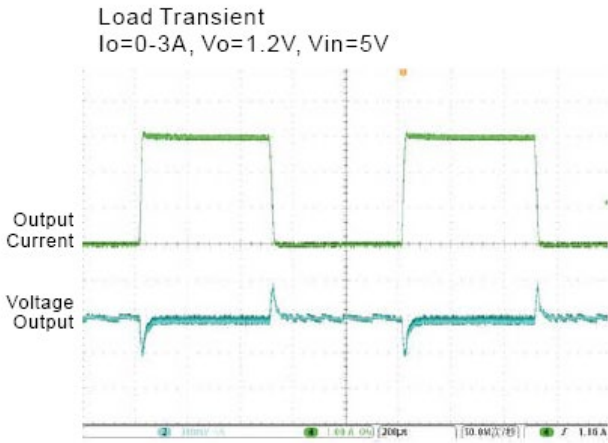


**Typical Performance Characteristics** (cont.) (@T<sub>A</sub> = +25°C, C<sub>IN</sub> = 22\*2μF, C<sub>O</sub> = 22μF, unless otherwise specified.)



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**Typical Performance Characteristics** (cont.) (@ $T_A = +25^\circ\text{C}$ ,  $C_{IN} = 22\mu\text{F}$ ,  $C_O = 22\mu\text{F}$ , unless otherwise specified.)





## Application Information

The basic PAM2307 application circuit is shown in Page 1. External component selection is determined by the load requirement, selecting L first and then C<sub>IN</sub> and C<sub>OUT</sub>.

### Inductor Selection

For most applications, the value of the inductor will fall in the range of 1μH to 2.7μH. Its value is chosen based on the desired ripple current and efficiency. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V<sub>IN</sub> or V<sub>OUT</sub> also increases the ripple current as shown in equation 3A reasonable starting point for setting ripple current is ΔI<sub>L</sub> = 1.2A (40% of 3A).

$$\Delta I_L = \frac{1}{fL} V_{OUT} \left( 1 - \frac{V_{OUT}}{V_{IN}} \right) \quad \text{Equation (1)}$$

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 4.2A rated inductor should be enough for most applications (3A + 1.2A). For better efficiency, choose a low DC-resistance inductor.

V <sub>O</sub>	1.2V	1.5V	1.8V	2.5V	3.3V
L	1.2μH	1.5μH	2.2μH	2.2μH	2.2μH

### C<sub>IN</sub> and C<sub>OUT</sub> Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle V<sub>OUT</sub>/V<sub>IN</sub>. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{IN \text{ required}} I_{RMS} \cong I_{OMAX} \frac{[V_{OUT}(V_{IN} - V_{OUT})]^{1/2}}{V_{IN}}$$

This formula has a maximum at V<sub>IN</sub> = 2V<sub>OUT</sub>, where I<sub>RMS</sub> = I<sub>OUT</sub> / 2. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Consult the manufacturer if there is any question.

The selection of C<sub>OUT</sub> is driven by the required effective series resistance (ESR).

Typically, once the ESR requirement for C<sub>OUT</sub> has been met, the RMS current rating generally far exceeds the I<sub>ripple</sub> (P-P) requirement. The output ripple ΔV<sub>OUT</sub> is determined by:

$$\Delta V_{OUT} \approx \Delta I_L (ESR + 1/8f C_{OUT})$$

Where f = operating frequency, C<sub>OUT</sub> = output capacitance and ΔI<sub>L</sub> = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since ΔI<sub>L</sub> increases with input voltage.

### Using Ceramic Input and Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

### Thermal Consideration

Thermal protection limits power dissipation in the PAM2307. When the junction temperature exceeds +150°C, the OTP (Over Temperature Protection) starts the thermal shutdown and turns the pass transistor off. The pass transistor resumes operation after the junction temperature drops below +120°C.

For continuous operation, the junction temperature should be maintained below +125°C. The power dissipation is defined as:

$$P_D = I_O^2 \frac{V_O R_{DS(ON)H} + (V_{IN} - V_O) R_{DS(ON)L}}{V_{IN}} + (t_{sw} F_s I_O + I_Q) V_{IN}$$

I<sub>Q</sub> is the step-down converter quiescent current. The term t<sub>sw</sub> is used to estimate the full load step-down converter switching losses.

## Application Information (cont.)

For the condition where the step-down converter is in dropout at 100% duty cycle, the total device dissipation reduces to:

$$P_D = I_O^2 R_{DS(ON)H} + I_Q V_{IN}$$

Since  $R_{DS(ON)}$ , quiescent current, and switching losses all vary with input voltage, the total losses should be investigated over the complete input voltage range. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surrounding airflow and temperature difference between junction and ambient. The maximum power dissipation can be calculated by the following formula:

$$P_D = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

Where  $T_{J(max)}$  is the maximum allowable junction temperature 125°C.  $T_A$  is the ambient temperature and  $\theta_{JA}$  is the thermal resistance from the junction to the ambient. Based on the standard JEDEC for a two layers thermal test board, the thermal resistance  $\theta_{JA}$  of QFN3x3 68°C/W and SOP-8(EP) 90°C/W respectively. The maximum power dissipation at  $T_A = +25^\circ\text{C}$  can be calculated by following formula:

$$P = (125^\circ\text{C} - 25^\circ\text{C}) / 68^\circ\text{C/W} = 1.47\text{W (QFN3X3)}$$

$$P = (125^\circ\text{C} - 25^\circ\text{C}) / 90^\circ\text{C/W} = 1.11\text{W (SOP-8)}$$

### Setting the Output Voltage

The internal reference is 0.6V (Typical). The output voltage is calculated as below:

The output voltage is given by Table 1.

$$V_O = 0.6 \times \left( 1 + \frac{R_1}{R_2} \right)$$

Table 1: Resistor selection for output voltage setting.

V <sub>o</sub>	R1	R2
1.2V	100k	100k
1.5V	150k	100k
1.8V	200k	100k
2.5V	380k	120k
3.3V	540k	120k

### 100% Duty Cycle Operation

As the input voltage approaches the output voltage, the converter turns the P-Channel transistor continuously on. In this mode the output voltage is equal to the input voltage minus the voltage drop across the P-Channel transistor:

$$V_{OUT} = V_{IN} - I_{LOAD} (R_{DS(ON)} + R_L)$$

where  $R_{DS(ON)}$  = P-Channel Switch ON Resistance,  $I_{LOAD}$  = Output Current,  $R_L$  = Inductor DC Resistance

### UVLO and Soft-Start

The reference and the circuit remain reset until the  $V_{IN}$  crosses its UVLO threshold.

The PAM2307 has an internal soft-start circuit that limits the in-rush current during start-up. This prevents possible voltage drops of the input voltage and eliminates the output voltage overshoot. The soft-start acts as a digital circuit to increase the switch current in several steps to the P-Channel current limit (1500mA).

### Short Circuit Protection

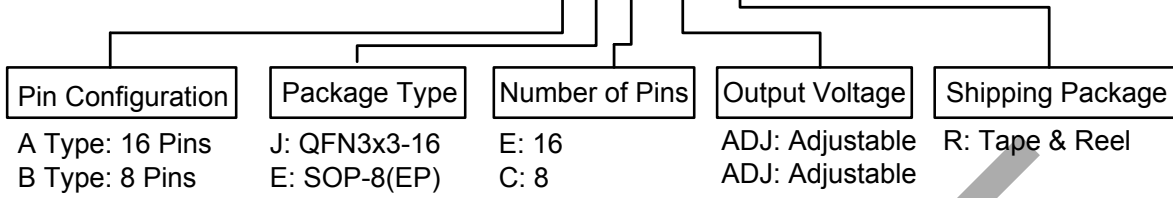
The switch peak current is limited cycle-by-cycle to a typical value of 1500mA. In the event of an output voltage short circuit, the device operates with a frequency of 400kHz and minimum duty cycle, therefore the average input current is typically 200mA.

### Thermal Shutdown

When the die temperature exceeds 150°C, a reset occurs and the reset remains until the temperature decrease to 120°C, at which time the circuit can be restarted.

**Ordering Information**

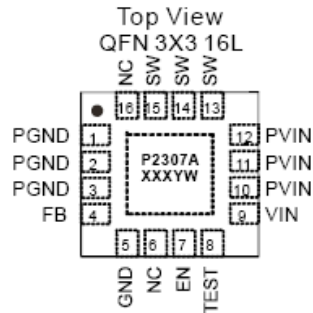
PAM2307 X X X xxx X



Part Number	Output Voltage	Part Type	Standard Package
PAM2307AJEADJR	ADJ	QFN3x3-16	3000 Units/Tape & Reel
PAM2307BECADJR	ADJ	SOP-8(EP)	2500 Units/Tape & Reel

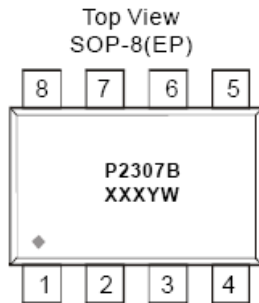
**Marking Information**

QFN3x3-16



A: Pin Configuration  
Y: Year  
W: Week  
X: Internal Code

SOP-8(EP)

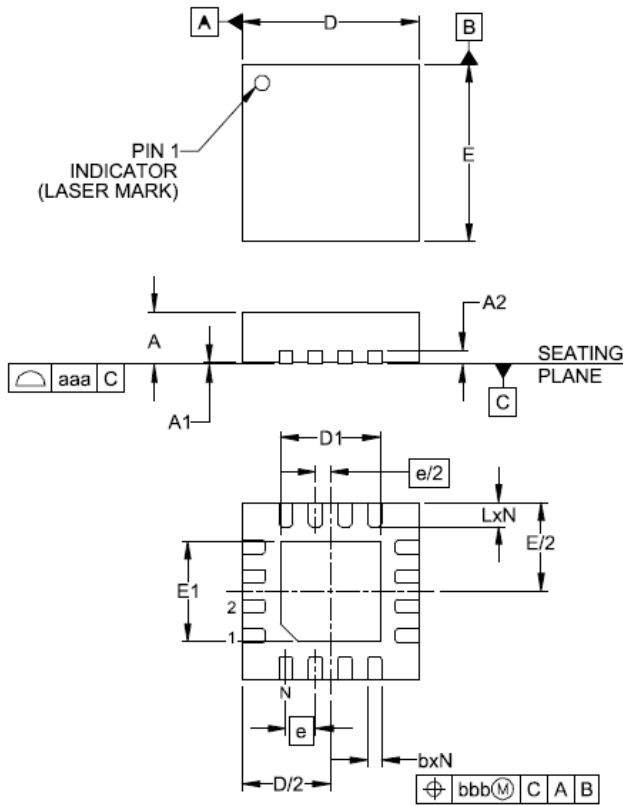


B: Pin Configuration  
Y: Year  
W: Week  
X: Internal Code

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**Package Outline Dimensions** (All dimensions in mm.)

QFN3x3-16



DIMENSIONS (Millimeters)			
	MIN	TYP	MAX
A	0.50	0.55	0.60
A1	0.00	0.02	0.05
A2	0.20		
b	0.18	0.25	0.30
D	2.90	3.00	3.10
D1	1.55	1.70	1.80
E	2.90	3.00	3.10
E1	1.55	1.70	1.80
e	0.50BSC		
L	0.30	0.40	0.50
N	16		
aaa	0.08		
bbb	0.10		

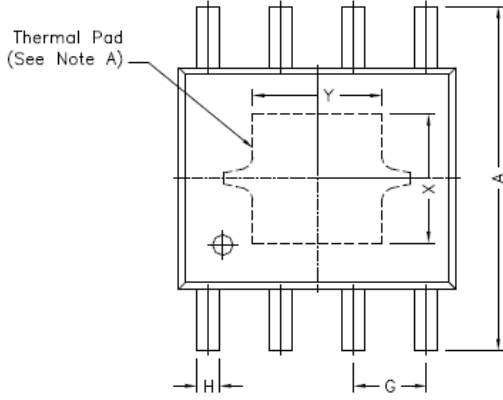
- Notes:
1. Controlling dimensions are in millimeters (angle in degrees).
  2. Coplanarity applies to the exposed pad as well as the terminals.
  3. DAP is 1.90 x 1.90mm.

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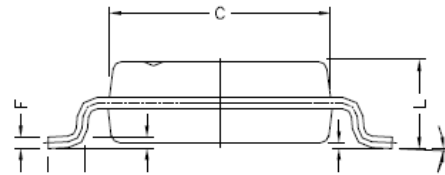
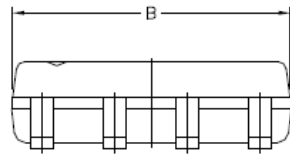
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**Package Outline Dimensions** (cont.) (All dimensions in mm.)

**SOP-8(EP)**



REF.	DIMENSIONS	
	Millimeters	
	Min.	Max.
A	5.80	6.20
B	4.80	5.00
C	3.80	4.00
D	0°	8°
E	0.40	0.90
F	0.19	0.25
M	0	0.15
H	0.35	0.49
L	1.35	1.75
G	1.27 TYP.	
Option1	X	2.28
	Y	2.28
Option2	X	2.41
	Y	3.30



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